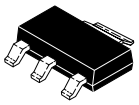
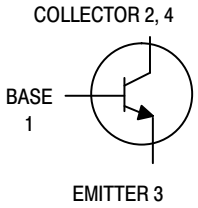
NPN Silicon Transistor

BF720T1G, SBF720T1G, BF720T3G

NPN SILICON TRANSISTOR SURFACE MOUNT



SOT−223 (TO−261)
CASE 318E
STYLE 1



Features

- AEC−Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	300	Vdc
Collector − Base Voltage	V_{CBO}	300	Vdc
Collector − Emitter Voltage	V_{CER}	300	Vdc
Emitter − Base Voltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	100	mAdc
Total Power Dissipation up to T_A = 25°C	P_D	1.5	W
Storage Temperature Range	T_{stg}	−65 to +150	°C
Junction Temperature	T_J	150	°C

THERMAL CHARACTERISTICS

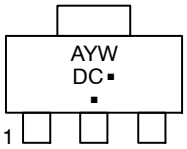
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	83.3	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 in^2.

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
DC = Device Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
BF720T1G	SOT−223 (Pb−Free)	1,000 / Tape & Reel
SBF720T1G	SOT−223 (Pb−Free)	1,000 / Tape & Reel

DISCONTINUED (Note 1)

BF720T3G	SOT−223 (Pb−Free)	4,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	300	–	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	300	–	Vdc
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, R_{BE} = 2.7 kΩ)	$V_{(BR)CER}$	300	–	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	–	Vdc
Collector-Base Cutoff Current (V_{CB} = 200 Vdc, I_E = 0)	I_{CBO}	–	10	nAdc
Collector–Emitter Cutoff Current (V_{CE} = 250 Vdc, R_{BE} = 2.7 kΩ) (V_{CE} = 200 Vdc, R_{BE} = 2.7 kΩ, T_J = 150°C)	I_{CER}	– –	50 10	nAdc μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 25 mAdc, V_{CE} = 20 Vdc)	h_{FE}	50	–	–
Collector-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	–	0.6	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 35 MHz)	f_T	60	–	MHz
Feedback Capacitance (V_{CE} = 30 Vdc, I_C = 0, f = 1.0 MHz)	C_{re}	–	1.6	pF

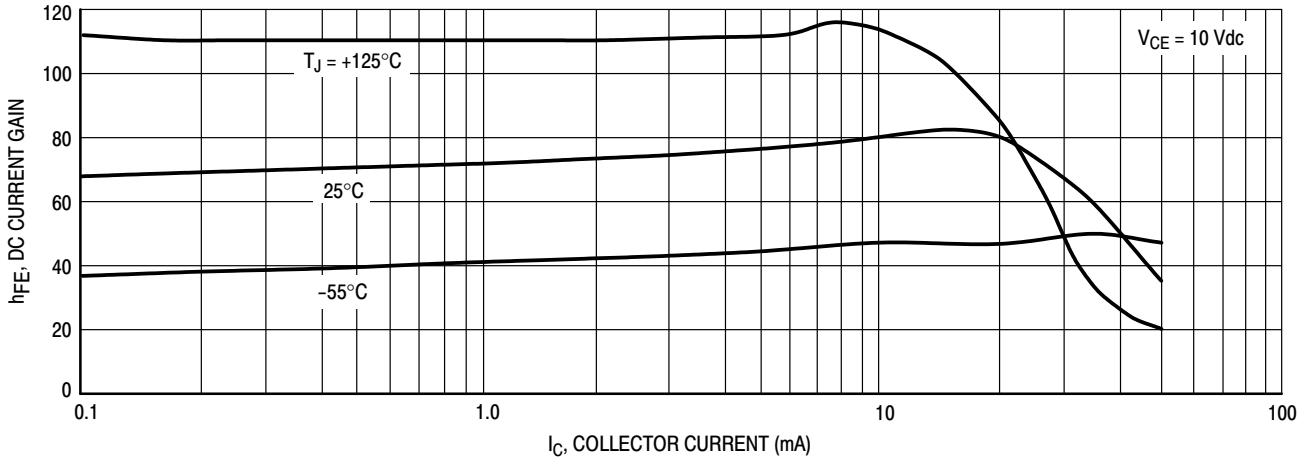


Figure 1. DC Current Gain

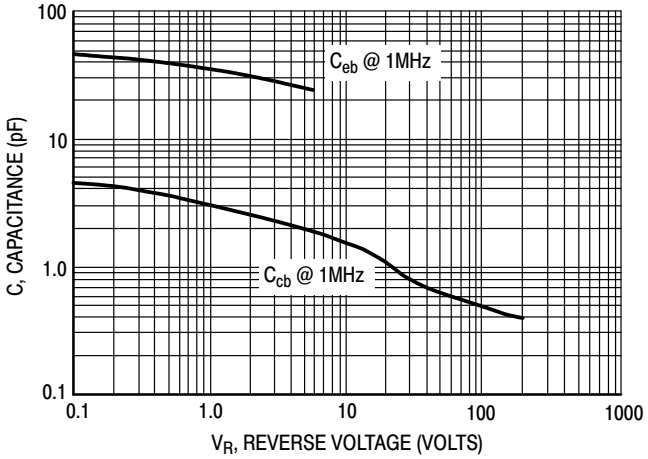


Figure 2. Capacitance

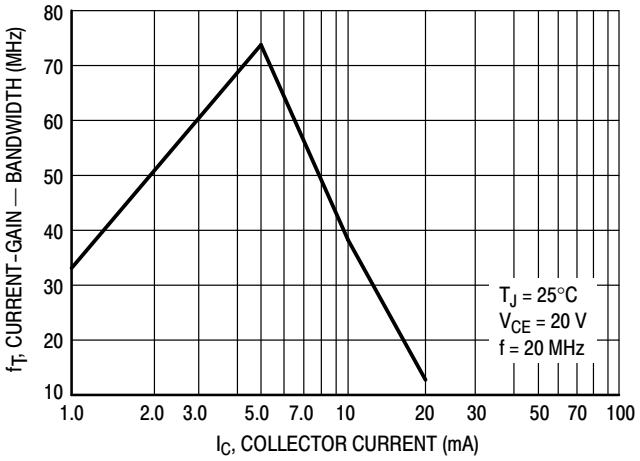


Figure 3. Current−Gain − Bandwidth

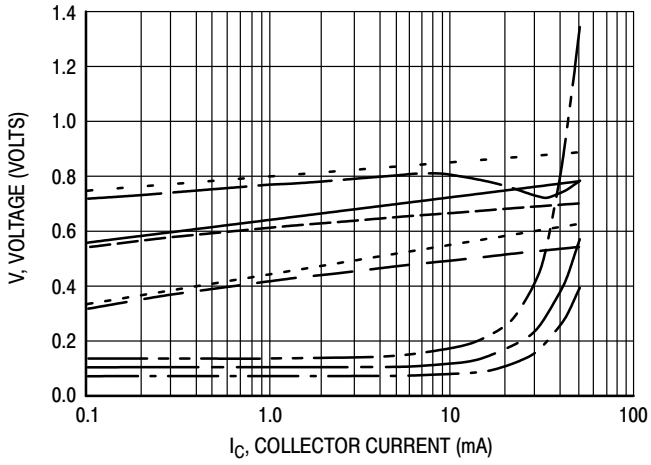
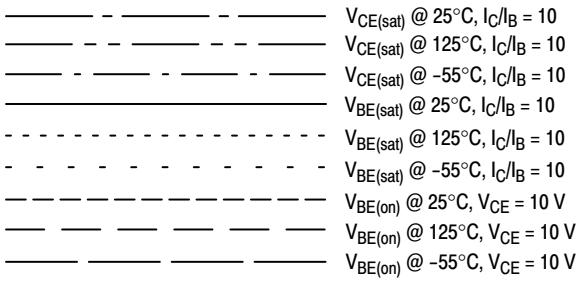


Figure 4. "ON" Voltages



ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales